

Marc Portail

List of Publications by Year in descending order

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603
citing authors

#	ARTICLE	IF	CITATIONS
1	Screening and engineering of colour centres in diamond. Journal Physics D: Applied Physics, 2018, 51, 483002.	1.3	66
2	Chondrules as direct thermochemical sensors of solar protoplanetary disk gas. Science Advances, 2018, 4, eaar3321.	4.7	57
3	AlGaIn/GaN high electron mobility transistors grown on 3C-SiC/Si(111). Journal of Crystal Growth, 2008, 310, 4417-4423.	0.7	41
4	p-Type Doping of 4H- and 3C-SiC Epitaxial Layers with Aluminum. Materials Science Forum, 0, 858, 137-142.	0.3	15
5	Micromachining of thin 3C-SiC films for mechanical properties investigation. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	14
6	Rotated domain network in graphene on cubic-SiC(001). Nanotechnology, 2014, 25, 135605.	1.3	14
7	Dynamical properties of graphite and peculiar behaviour of the low-energy plasmon. Surface Science, 1999, 433-435, 863-867.	0.8	13
8	Recent Advances in Surface Preparation of Silicon Carbide and other Wide Band Gap Materials. Materials Science Forum, 0, 645-648, 753-758.	0.3	13
9	Influence of 3C-SiC/Si(111) template properties on the strain relaxation in thick GaN films. Journal of Crystal Growth, 2014, 398, 23-32.	0.7	13
10	Direct insight into grains formation in Si layers grown on 3C-SiC by chemical vapor deposition. Acta Materialia, 2015, 98, 336-342.	3.8	13
11	Structural Quality, Polishing and Thermal Stability of 3C-SiC/Si Templates. Materials Science Forum, 0, 924, 306-309.	0.3	12
12	X-Ray Diffraction and Raman Spectroscopy Study of Strain in Graphene Films Grown on 6H-SiC(0001) Using Propane-Hydrogen-Argon CVD. Materials Science Forum, 0, 740-742, 117-120.	0.3	10
13	Investigation of structural and electronic properties of epitaxial graphene on 3C-SiC(100)/Si(100) substrates. Nanotechnology, Science and Applications, 2014, 7, 85.	4.6	10
14	Study by HREELS of elementary reactions on graphite surface induced by Ar ⁺ and H ⁺ ion bombardment. Surface Science, 2000, 454-456, 384-389.	0.8	8
15	Low Specific Contact Resistance to 3C-SiC Grown on (100) Si Substrates. Materials Science Forum, 2007, 556-557, 721-724.	0.3	8
16	Role of Substrate Misorientation in Relaxation of 3C-SiC Layers on Silicon. Materials Science Forum, 0, 615-617, 169-172.	0.3	8
17	A comparative study of graphene growth on SiC by hydrogen-CVD or Si sublimation through thermodynamic simulations. CrystEngComm, 2018, 20, 3702-3710.	1.3	8
18	Metalorganic Chemical Vapor Phase Epitaxy Growth of Buffer Layers on 3C-SiC/Si(111) Templates for AlGaIn/GaN High Electron Mobility Transistors with Low RF Losses. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900760.	0.8	8

#	ARTICLE	IF	CITATIONS
19	Elaboration of Monocrystalline Si Thin Film on 3C-SiC(100)/Si Epilayers by Low Pressure Chemical Vapor Deposition. Materials Science Forum, 0, 711, 61-65.	0.3	7
20	Trends in Dopant Incorporation for 3C-SiC Films on Silicon. Materials Science Forum, 0, 556-557, 207-210.	0.3	6
21	Structural and Morphological Characterization of 3C-SiC Films Grown on (111), (211) and (100) Silicon Substrates. Materials Science Forum, 2008, 600-603, 231-234.	0.3	6
22	Electrical Characterization of Nitrogen Implanted 3C-SiC by SSRM and CÂTLM Measurements. Materials Science Forum, 0, 679-680, 193-196.	0.3	6
23	Toward high-quality 3C-SiC membrane on a 3C-SiC pseudo-substrate. Materials Letters, 2015, 160, 28-30.	1.3	6
24	GaN films and GaN/AlGaIn quantum wells grown by plasma assisted molecular beam epitaxy using a high density radical source. Journal of Crystal Growth, 2016, 433, 165-171.	0.7	6
25	Strain in 3C-SiC Heteroepitaxial Layers Grown on (100) and (111) Oriented Silicon Substrates. Materials Science Forum, 2008, 600-603, 207-210.	0.3	5
26	Ti Thickness Influence for Ti/Ni Ohmic Contacts on N-Type 3C-SiC. Materials Science Forum, 2012, 711, 179-183.	0.3	5
27	Silicon Growth on 3C-SiC(001)/Si(001): Pressure Influence and Thermal Effect. Materials Science Forum, 0, 821-823, 978-981.	0.3	5
28	Turning the undesired voids in silicon into a tool: In-situ fabrication of free-standing 3C-SiC membranes. Applied Physics Letters, 2017, 110, 081602.	1.5	5
29	A detailed study of AlN and GaN grown on silicon-on-porous silicon substrate. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600450.	0.8	5
30	Epitaxial Graphene Elaborated on 3C-SiC(111)/Si Epilayers. Materials Science Forum, 2010, 645-648, 585-588.	0.3	4
31	Dose Influence on Physical and Electrical Properties of Nitrogen Implantation in 3C-SiC on Si. Materials Science Forum, 0, 711, 154-158.	0.3	4
32	Graphene/SiC Interface Control Using Propane-Hydrogen CVD on 6H-SiC(0001) and 3C-SiC(111)/Si(111). Materials Science Forum, 2012, 711, 253-257.	0.3	4
33	Realization of minimum number of rotational domains in heteroepitaxied Si(110) on 3C-SiC(001). Applied Physics Letters, 2016, 108, 011608.	1.5	4
34	CVD Growth of Graphene on SiC (0001): Influence of Substrate Offcut. Materials Science Forum, 0, 897, 731-734.	0.3	4
35	Pendeo-epitaxy of GaN on SOI nano-pillars: Freestanding and relaxed GaN platelets on silicon with a reduced dislocation density. Journal of Crystal Growth, 2019, 526, 125235.	0.7	4
36	Analytical Model of Stress Relaxation in 3C SiC Layers on Silicon. Materials Science Forum, 2011, 679-680, 79-82.	0.3	3

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37	Structural and Electrical Properties of Graphene Films Grown by Propane/Hydrogen CVD on 6H-SiC(0001). Materials Science Forum, 0, 717-720, 625-628.	0.3	3
38	Investigation of Aluminum Incorporation in 4H-SiC Epitaxial Layers. Materials Science Forum, 0, 806, 45-50.	0.3	3
39	3C-SiC: New Interest for MEMS Devices. Materials Science Forum, 0, 806, 3-9.	0.3	3
40	On the interplay between Si(110) epilayer atomic roughness and subsequent 3C-SiC growth direction. Journal of Applied Physics, 2016, 120, .	1.1	3
41	Influence of Aluminum Incorporation on Mechanical Properties of 3C-SiC Epilayers. Materials Science Forum, 0, 924, 318-321.	0.3	3
42	P Implantation Effect on Specific Contact Resistance in 3C-SiC Grown on Si. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	2
43	Advances in Liquid Phase Conversion of (100) and (111) Oriented Si Wafers into Self-Standing 3C-SiC. Materials Science Forum, 0, 615-617, 49-52.	0.3	2
44	Thermally Induced Surface Reorganization of 3C-SiC(111) Epilayers Grown on Silicon Substrates. Materials Science Forum, 2010, 645-648, 155-158.	0.3	2
45	Structural Study of the Innovative 3C-SiC/Si/3C-SiC/Si Heterostructure for Electro-Mechanical Applications. Materials Science Forum, 0, 858, 143-146.	0.3	2
46	Buried defects induced by plasma assisted molecular beam epitaxy of AlN and GaN on Silicon. Journal of Crystal Growth, 2019, 507, 220-225.	0.7	2
47	Oxygen isotope variations in Mg-rich olivines from type I chondrules in carbonaceous chondrites. Geochimica Et Cosmochimica Acta, 2022, 319, 73-93.	1.6	2
48	Designing SiC Based CMUT Structures: An Original Approach and Related Material Issues. Materials Science Forum, 0, 1062, 94-98.	0.3	2
49	Detailed Experimental Study of Mean and Gradient Stresses in Thin 3C-SiC Films Performed Using Micromachined Cantilevers. Materials Science Forum, 2012, 711, 84-88.	0.3	1
50	CVD Growth of Graphene on 2â€™™â€™™ 3C-SiC/Si Templates: Influence of Substrate Orientation and Wafer Homogeneity. Materials Science Forum, 0, 717-720, 621-624.	0.3	1
51	Influence of Site Competition Effects on Dopant Incorporation during Chemical Vapor Deposition of 4H-SiC Epitaxial Layers. Materials Science Forum, 2015, 821-823, 149-152.	0.3	1
52	Novel 3C-SiC Microstructure for MEMS Applications. Materials Science Forum, 2016, 858, 723-728.	0.3	1
53	Precise Control of Al Incorporation during CVD Growth of SiC Epilayers by Using Hydrogen Chloride. Materials Science Forum, 0, 1062, 84-88.	0.3	1
54	Structural Investigation of Si Quantum Dots Grown by CVD on AlN/Si(111) and 3C-SiC/Si(100) Epilayers. Materials Science Forum, 2015, 821-823, 1003-1006.	0.3	0

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55	Ion-induced interdiffusion of surface GaN quantum dots. Nuclear Instruments & Methods in Physics Research B, 2017, 409, 107-110.	0.6	0
56	Influence of Growth Temperature on Site Competition Effects during Chemical Vapor Deposition of 4H-SiC Layers. Materials Science Forum, 2017, 897, 79-82.	0.3	0
57	Vanadium Incorporation in 3C-SiC Epilayers and its Consequences for Electrical Properties of 3C-SiC Material. Materials Science Forum, 0, 1062, 140-145.	0.3	0
58	AlGaIn/GaN High Electron Mobility Transistors Grown by MOVPE on 3C-SiC/Si(111) for RF Applications. Materials Science Forum, 0, 1062, 482-486.	0.3	0